What is claimed is:

1. A method of manufacturing a circuit device comprising the steps of:

preparing a conductive foil and forming an isolation trench having a smaller thickness than that of the conductive foil on the conductive foil in a region excluding a conductive pattern of a first layer, thereby forming the conductive pattern of the first layer;

forming plural layers of a conductive pattern on the conductive pattern of the first layer through an interlayer insulating film;

incorporating a circuit element into the conductive pattern which is desirable;

covering the circuit element and entirely molding with an insulating resin; and

removing the conductive foil in a thick portion where the isolation trench is not provided.

2. A method of manufacturing a circuit device according to claim 1 further comprising the step of:

separating the insulating resin through dicing for each circuit device including the circuit element.

3. The method of manufacturing a circuit device

according to claim 1, wherein the conductive foil is constituted by any of copper, aluminum and iron-nickel.

4. The method of manufacturing a circuit device according to claim 1, wherein the isolation trench to be selectively formed on the conductive foil is provided through chemical or physical etching.

5. The method of manufacturing a circuit device according to claim 1, wherein a thermosetting resin is used for the interlayer insulating film.

6. The method of manufacturing a circuit device according to claim 5, wherein a via hole is formed on the interlayer insulating film through a laser.

7. The method of manufacturing a circuit device according to claim 1, wherein a photosensitive resist layer is used for the interlayer insulating film.

8. The method of manufacturing a circuit device according to claim 7, wherein a via hole is formed on the interlayer insulating film through photosensitization.

9. The method of manufacturing a circuit device

according to claim 1, wherein the conductive pattern of the layers is formed by a copper plated layer.

10. The method of manufacturing a circuit device according to claim 9, wherein the copper plated layer is formed by electroless plating and electroplating.

11. The method of manufacturing a circuit device according to claim 1, wherein the circuit element has either or both of a semiconductor bare chip and a chip circuit component fixed thereto.

12. The method of manufacturing a circuit device according to claim 1, wherein the insulating resin is molded by transfer molding or potting.

13. A method of manufacturing a circuit device comprising the steps of:

preparing a conductive foil and forming plural layers of a conductive pattern through an interlayer insulating film;

incorporating a circuit element into the conductive pattern which is desirable;

covering the circuit element and molding a whole surface with an insulating resin; and

removing the conductive foil.

14. A method of manufacturing a circuit device according to claim 13 further comprising the step of:

isolating the insulating resin through dicing for each circuit device including the circuit element.

15 The method of manufacturing a circuit device according to claim 13, wherein the conductive foil is constituted by any of copper, aluminum and iron-nickel.

16. The method of manufacturing a circuit device according to claim 13, wherein a thermosetting resin is used for the interlayer insulating film.

17. The method of manufacturing a circuit device according to claim 16, wherein a via hole is formed on the interlayer insulating film through a laser.

18. The method of manufacturing a circuit device according to claim 13, wherein a photosensitive resist layer is used for the interlayer insulating film.

19. The method of manufacturing a circuit device according to claim 18, wherein a via hole is formed on the interlayer insulating film through photosensitization.

20. The method of manufacturing a circuit device according to claim 13, wherein the conductive pattern of the layers is formed by a copper plated layer.

21. The method of manufacturing a circuit device according to claim 20, wherein the copper plated layer is formed by electroless plating and electroplating.

22. The method of manufacturing a circuit device according to claim 13, wherein the circuit element has either or both of a semiconductor bare chip and a chip circuit component fixed thereto.

23. The method of manufacturing a circuit device according to claim 13, wherein the insulating resin is molded by transfer molding or potting.